Information on sensor products

Features

From production of the detector element to assembly of the final product, ROHM handles all stages of our photosensor manufacturing process. This allows precise control of sensitivity, output power, and other characteristics. ROHM infrared LEDs and phototransistors are available in a wide variety of packages to meet the diverse needs of our customers. We apply a silicon coating to all of our infrared LED chips to ensure long term reliability.

ROHM is a pioneer in the development of double-layer molding photointerrupters. The use of single chip molded technology in place of the conventional casing method has allowed us to attain an ultra-small package. These photointerrupters will undoubtedly make a significant contribution to the development of increasingly lightweight and compact devices.

Explanation of symbols

(1) General symbols

Term	Symbol	Explanation
Absolute maximum rating		A limiting value which must not be exceeded even instantaneously.
Ambient temperature	Та	Temperature of the environment of a semiconductor element.
Operating temperature	Topr	Ambient temperature when a semiconductor element is operating.
Storage temperature	Tstg	Temperature at which a semiconductor element should be stored.
Soldering temperature	Tsol	Temperature at which designated parts of a terminal can be soldered.

(2) Symbols related to infrared LEDs, photointerrupters and photoreflectors

Term	Symbol	Explanation
Power dissipation	P□	Maximum allowable power dissipation of infared LEDs.
Forward current	lF	Direct current flowing forward through infared LEDs.
Peak forward current	IFP	Maximum instantaneous value of forward current.
Forward voltage	VF	Voltage drop between anode and cathode due to forward current.
Peak forward voltage	VFP	Maximum instantaneous value of voltage drop between anode and cathode due to peak forward current.
Reverse current	la	Current flowing in reverse direction between anode and cathode.
Reverse voltage	VR	Voltage applied in reverse direction between anode and cathode.
Capacitance between terminals	Ct	Capacitance between anode and cathode terminaes.
Peak light emitting wavelength	λР	Wavelength of maximum radiant intensity.
Spectral line half width	Δλ	Spectral bandwidth in which radiant intensity is 50% or more of peak value.
Half-viewing angle	θ 1/2	Angle at which radiant intensity is 50% of the peak value.

(3) Symbols related to, phototransistors, photo IC's, photointerrupters and photoreflectors

Term	Symbol	Explanation
Collector-emitter voltage	Vceo	DC voltage from collector to emitter when base terminal is open.
Emitter-collector voltage	VECO	DC voltage from emitter to collector when base terminal is open.
Collector-base voltage	Vсво	DC voltage from collector to base when emitter terminal is open.
Emitter-base voltage	VEBO	DC voltage from emitter to base when collector terminal is open.
Reverse voltage	VR	DC voltage applied in reverse direction between anode and cathode.
Collector power dissipation	Pc	Maximum power dissipation of collector.
Power dissipation	P□	Maximum allowable power dissipation between anode and cathode.
Collector current	lc	Direct current flowing to collector terminal.
Dark current	Iceo	Collector current which flows when base terminal is open and reverse voltage is applied between collector and emitter.
	la	Current which flows when reverse voltage is applied to diode when shielded from light.
Illuminance	Ev	Incident luminous flux per unit area.
Irradiance	E₀	Incident radiation flux per unit area.
	Evlh	The employed five diagraph when the output goes from low to high as from high to
Threshold irradiance	or	The amount of irradiance when the output goes from low to high, or from high to low.
	EvhL	
Direct current amplification	hfe	The direct current amplification when the emitter is grounded.
Collector-emitter saturation voltage	VCE (sat)	DC voltage from collector to emitter under specified saturation conditions.
Capacitance between terminals	Ct	Electrostatic capacitance between anode and cathode terminals.
Peak sensitivity wavelength	λP	Wavelength of incident light at which sensitivity is greatest.
Half angle	θ 1/2	Angle at which sensitivity is 50% of peak value.
Cutoff frequency	fc	When the frequency of the constant-amplitude sine wave component of the input parameter is changed, this is the frequency which causes a 3 dB drop in the amplitude of the base AC wave of the corresponding output parameter.
Response time	tr tr	Time required for output to respond to input. Rise time: tr Delay time: td Fall time: tr Store time: ts Turn-on time: ton = td + tr Turn-off time: tor = ts + tr Low-to-high propagation time: tPLH High-to-low propagation time: tPHL
Threshold input current	IFLH Or IFHL	Input current when output level goes from low to high, or high to low.

Term	Symbol	Explanation
Output low level voltage	Vol	Output voltage when a designated low level output current is applied to output terminal.
Output high level voltage	Vон	Output voltage when a designated high level output current is applied to output terminal.
Output low level current	loL	Output voltage when a designated low level output voltage is applied to output terminal.
High level output current	Іон	Output voltage when a designated high level output voltage is applied to output terminal.
Low level power supply current	Iccl	Supply current which flows when output level is low.
High level power supply current	Іссн	Supply current which flows when output level is high.
Hysteresis	IFLH / IFHL Or IFHL / IFLH	The ratio of the threshold input current when the output level goes from low to high to the threshold input current when the output goes from high to low.

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